

# General Purpose PNP Epitaxial Planar Transistor

## BCP53L3

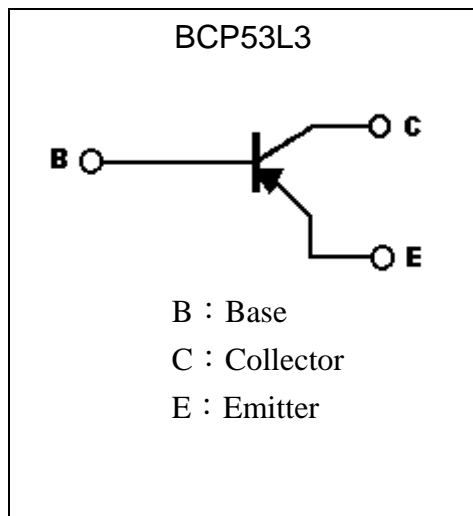
### Description

General purpose mainly intended for use in medium power industrial application and for audio amplifier output stage.

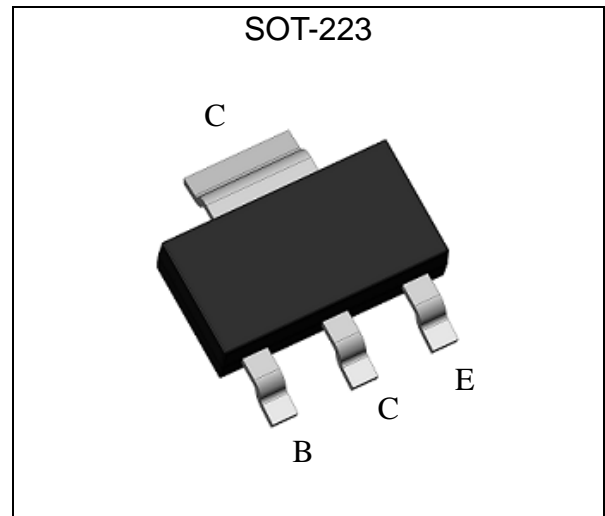
### Features

- High collector current and low  $V_{CE(SAT)}$
- Complement to BCP56L3
- Pb-free lead plating package

### Symbol

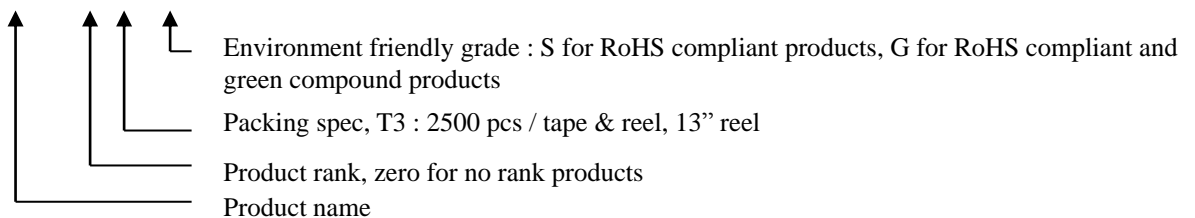


### Outline



### Ordering Information

| Device          | Package                                   | Shipping               |
|-----------------|---|------------------------|
| BCP53L3-XX-T3-G | SOT-223<br>(Pb-free lead plating package) | 2500 pcs / tape & reel |





**Absolute Maximum Ratings** (Ta=25°C)

| Parameter                               | Symbol           | Limits   | Unit |
|---|------------------|----------|------|
| Collector-Base Voltage                  | V <sub>CB0</sub> | -100     | V    |
| Collector-Emitter Voltage               | V <sub>CEO</sub> | -80      | V    |
| Emitter-Base Voltage                    | V <sub>EB0</sub> | -5       | V    |
| Collector Current(DC)                   | I <sub>C</sub>   | -1       | A    |
| Collector Current(Pulse)                | I <sub>CP</sub>  | -1.5     | A    |
| Power Dissipation @T <sub>C</sub> =25°C | P <sub>d</sub>   | 2        | W    |
| Junction Temperature                    | T <sub>j</sub>   | 150      | °C   |
| Storage Temperature                     | T <sub>stg</sub> | -55~+150 | °C   |

**Characteristics** (Ta=25°C)

| Symbol                 | Min. | Typ.  | Max. | Unit | Test Conditions  |
|------------------------|------|-------|------|------|--|
| BV <sub>CB0</sub>      | -100 | -     | -    | V    | I <sub>C</sub> =-100μA                                 |
| BV <sub>CEO</sub>      | -80  | -     | -    | V    | I <sub>C</sub> =-10mA                                  |
| BV <sub>EB0</sub>      | -5   | -     | -    | V    | I <sub>E</sub> =-10μA                                  |
| I <sub>CB0</sub>       | -    | -     | -100 | nA   | V <sub>CB</sub> =-80V                                  |
| I <sub>EB0</sub>       | -    | -     | -100 | nA   | V <sub>EB</sub> =-5V                                   |
| *V <sub>CE(sat)1</sub> | -    | -0.16 | -0.3 | V    | I <sub>C</sub> =-500mA, I <sub>B</sub> =-50mA          |
| *V <sub>CE(sat)2</sub> | -    | -     | -0.6 | V    | I <sub>C</sub> =-700mA, I <sub>B</sub> =-35mA          |
| *V <sub>BE(sat)</sub>  | -    | -     | -1.2 | V    | I <sub>C</sub> =-1A, I <sub>B</sub> =-50mA             |
| *V <sub>BE(on)</sub>   | -    | -     | -1.0 | V    | V <sub>CE</sub> =-2V, I <sub>C</sub> =-500mA           |
| *h <sub>FE1</sub>      | 100  | -     | -    | -    | V <sub>CE</sub> =-2V, I <sub>C</sub> =-5mA             |
| *h <sub>FE2</sub>      | 100  | -     | 400  | -    | V <sub>CE</sub> =-2V, I <sub>C</sub> =-150mA           |
| *h <sub>FE3</sub>      | 50   | -     | -    | -    | V <sub>CE</sub> =-2V, I <sub>C</sub> =-500mA           |
| f <sub>T</sub>         | -    | 125   | -    | MHz  | V <sub>CE</sub> =-10V, I <sub>C</sub> =-50mA, f=100MHz |
| C <sub>ob</sub>        | -    | -     | 10   | pF   | V <sub>CB</sub> =-10V, I <sub>E</sub> =0A, f=1MHz      |

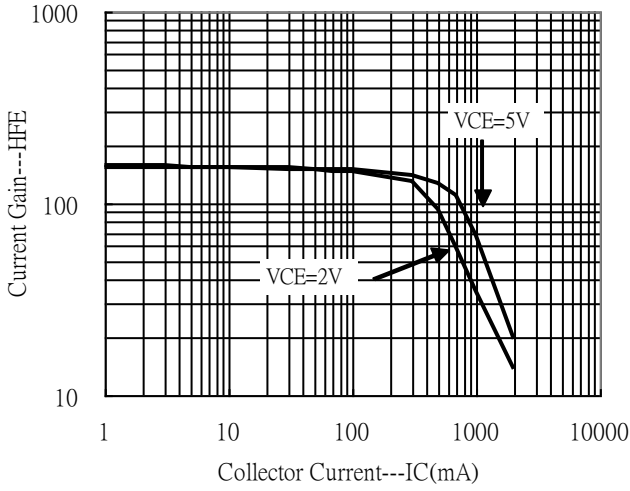
\*Pulse Test: Pulse Width ≤380μs, Duty Cycle≤2%

**Classification Of h<sub>FE</sub> 2**

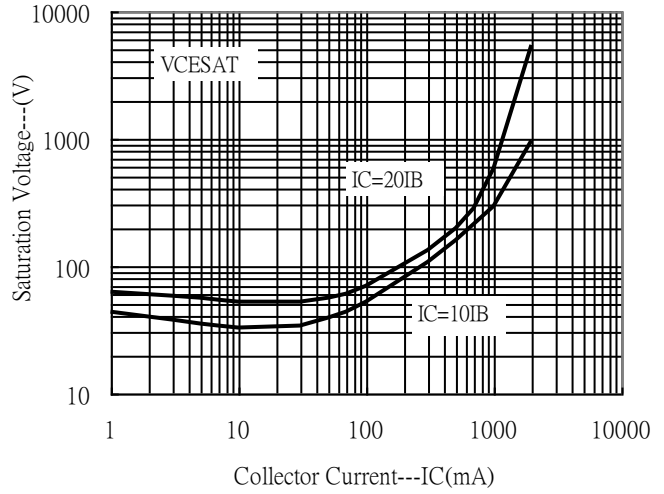
|       |         |         |
|-------|---------|---------|
| Rank  | -16     | -25     |
| Range | 100~250 | 160~400 |

**Typical Characteristics**

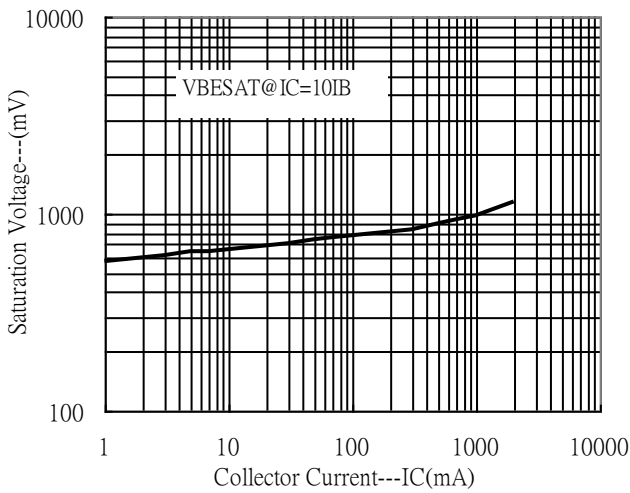
Current Gain vs Collector Current



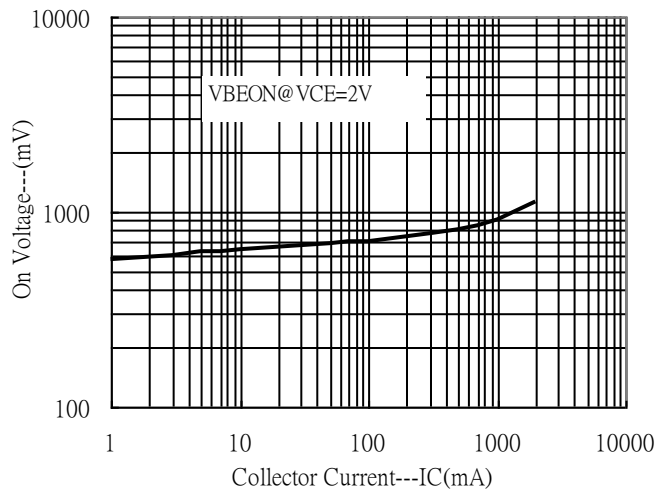
Saturation Voltage vs Collector Current



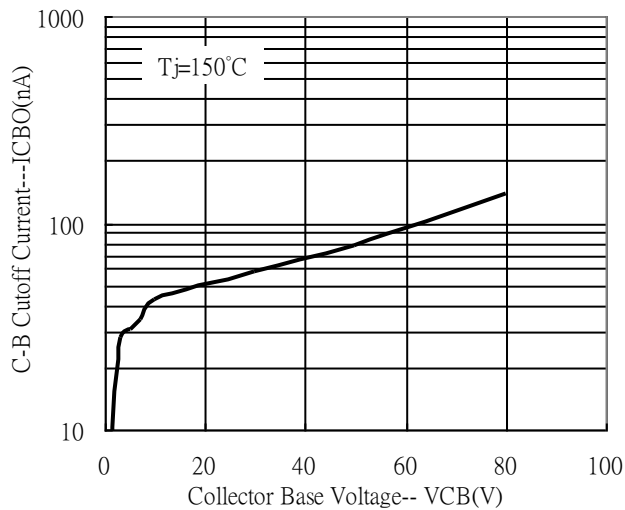
Saturation Voltage vs Collector Current



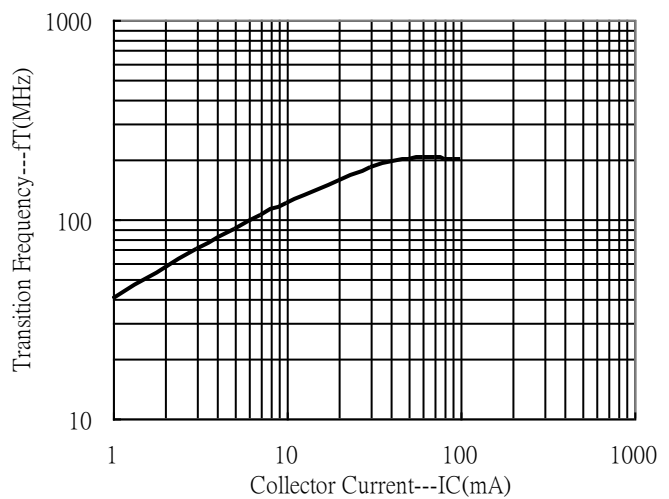
On Voltage vs Collector Current



Typical Cutoff Current Characteristics

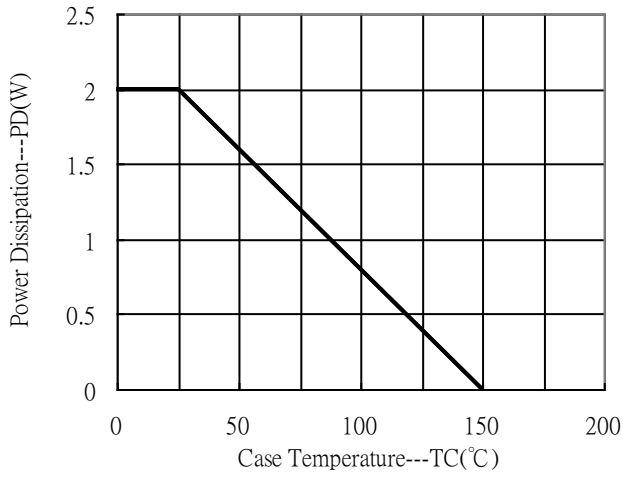


Transition Frequency vs Collector Current

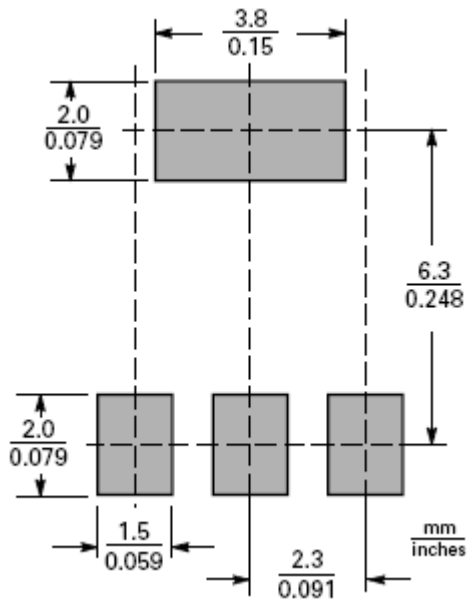


**Typical Characteristics(Cont.)**

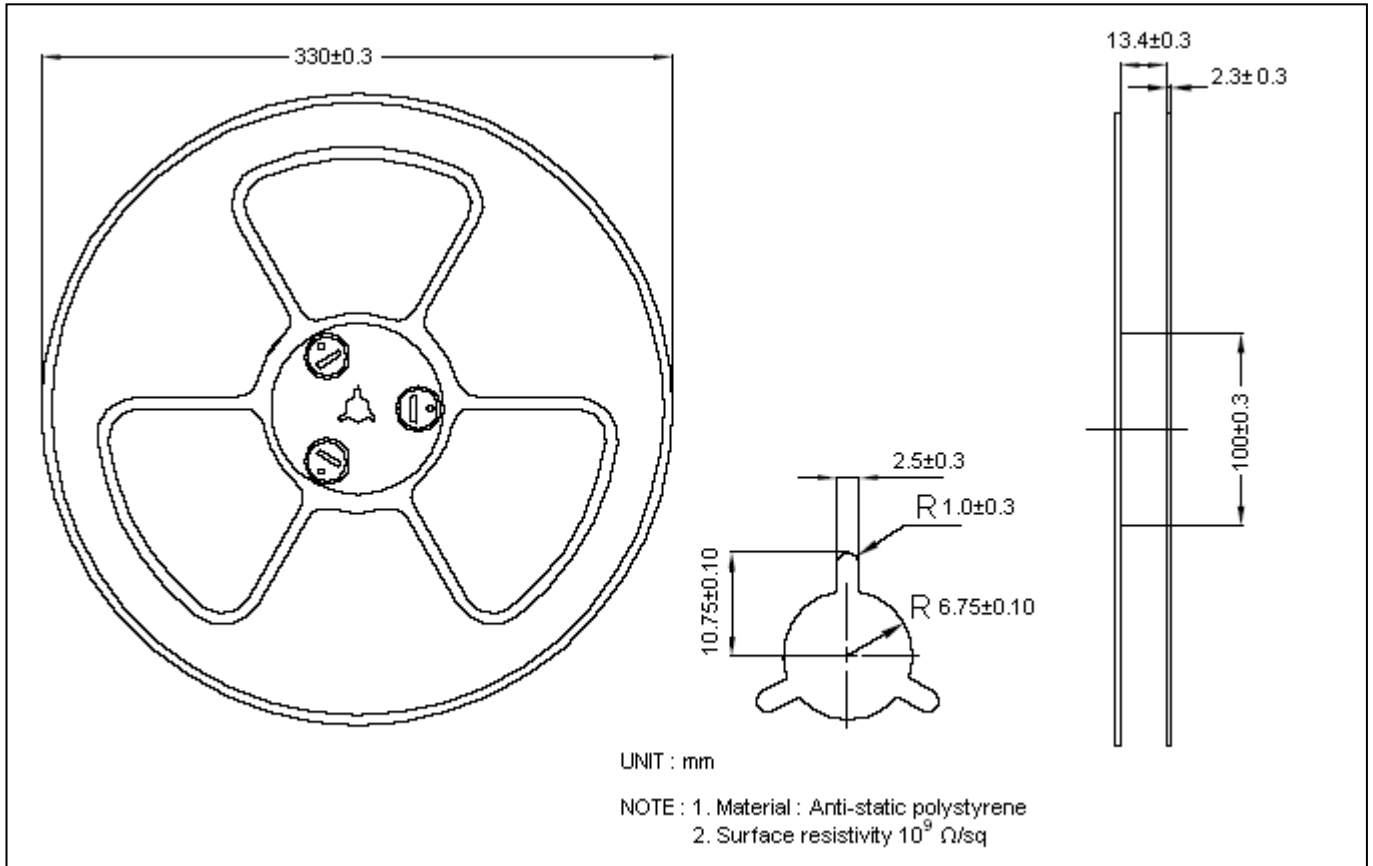
Power Derating Curve



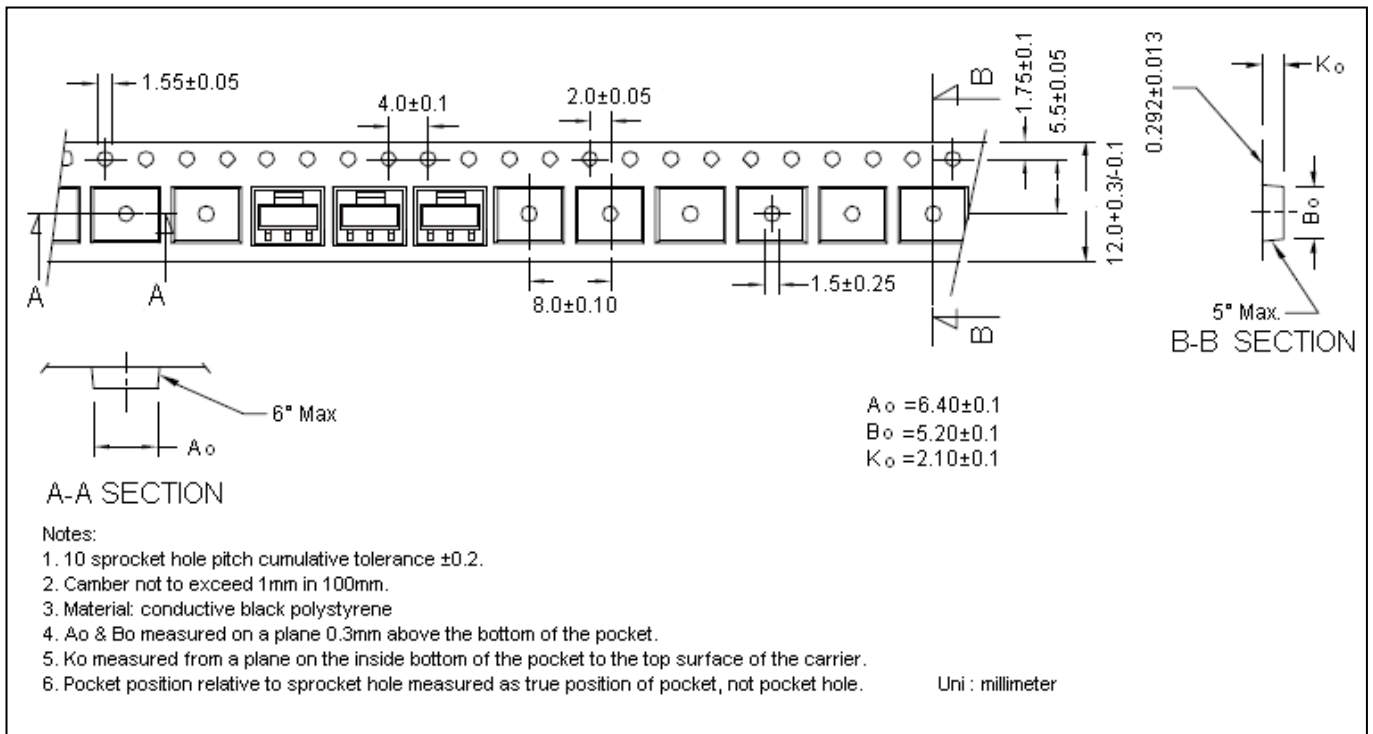
**Recommended soldering footprint**



**Reel Dimension**



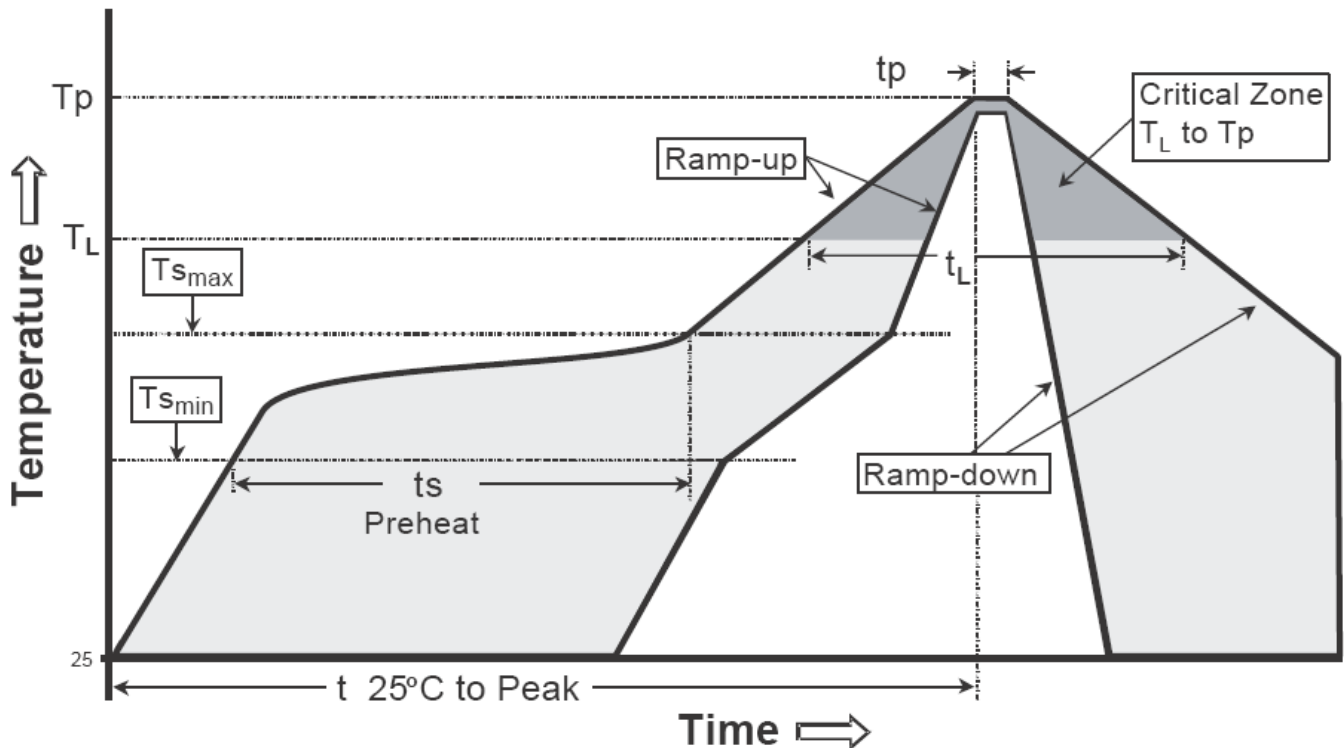
**Carrier Tape Dimension**



**Recommended wave soldering condition**

|                 |                  |                 |
|-----------------|------------------|-----------------|
| Product         | Peak Temperature | Soldering Time  |
| Pb-free devices | 260 +0/-5 °C     | 5 +1/-1 seconds |

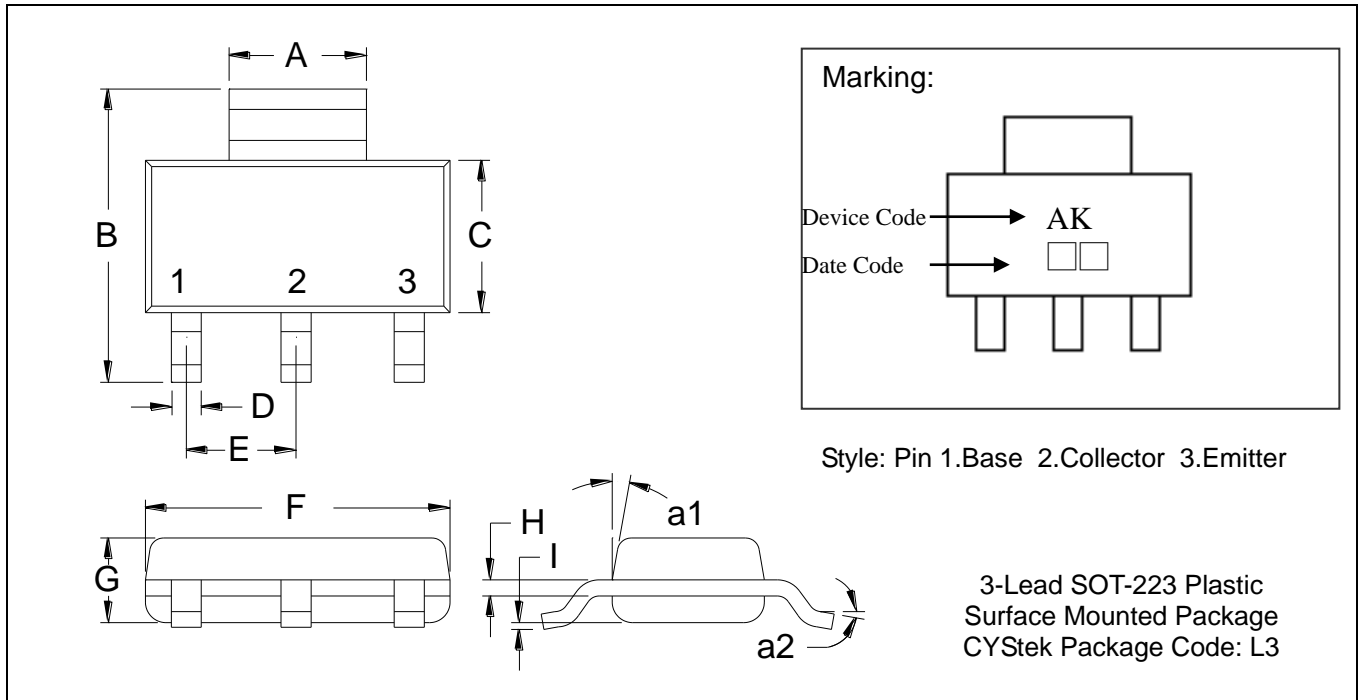
**Recommended temperature profile for IR reflow**



| Profile feature                                | Sn-Pb eutectic Assembly | Pb-free Assembly |
|--|-------------------------|------------------|
| Average ramp-up rate (Tsmax to Tp)             | 3°C/second max.         | 3°C/second max.  |
| Preheat  |                         |                  |
| -Temperature Min(Ts min)                       | 100°C                   | 150°C            |
| -Temperature Max(Ts max)                       | 150°C                   | 200°C            |
| -Time(ts min to ts max)                        | 60-120 seconds          | 60-180 seconds   |
| Time maintained above:                         |                         |                  |
| -Temperature (TL)                              | 183°C                   | 217°C            |
| - Time (tL)                                    | 60-150 seconds          | 60-150 seconds   |
| Peak Temperature(TP)                           | 240 +0/-5 °C            | 260 +0/-5 °C     |
| Time within 5°C of actual peak temperature(tp) | 10-30 seconds           | 20-40 seconds    |
| Ramp down rate                                 | 6°C/second max.         | 6°C/second max.  |
| Time 25 °C to peak temperature                 | 6 minutes max.          | 8 minutes max.   |

Note : All temperatures refer to topside of the package, measured on the package body surface.

**SOT-223 Dimension**



\*: Typical

| DIM | Inches  |        | Millimeters |      | DIM | Inches |        | Millimeters |      |
|-----|---------|--------|-------------|------|-----|--------|--------|-------------|------|
|     | Min.    | Max.   | Min.        | Max. |     | Min.   | Max.   | Min.        | Max. |
| A   | 0.1142  | 0.1220 | 2.90        | 3.10 | G   | 0.0551 | 0.0709 | 1.40        | 1.80 |
| B   | 0.2638  | 0.2874 | 6.70        | 7.30 | H   | 0.0098 | 0.0138 | 0.25        | 0.35 |
| C   | 0.1299  | 0.1457 | 3.30        | 3.70 | I   | 0.0008 | 0.0039 | 0.02        | 0.10 |
| D   | 0.0236  | 0.0315 | 0.60        | 0.80 | a1  | *13°   | -      | *13°        | -    |
| E   | *0.0906 | -      | *2.30       | -    | a2  | 0°     | 10°    | 0°          | 10°  |
| F   | 0.2480  | 0.2638 | 6.30        | 6.70 |     |        |        |             |      |

- Notes: 1.Controlling dimension: millimeters.  
 2.Maximum lead thickness includes lead finish thickness, and minimum lead thickness is the minimum thickness of base material.  
 3.If there is any question with packing specification or packing method, please contact your local CYStek sales office.

**Material:**

- Lead: Pure tin plated.
- Mold Compound: Epoxy resin family, flammability solid burning class: UL94V-0

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